

TrenchT2™ Power MOSFET

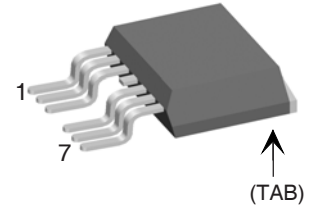
IXTA230N075T2-7

$V_{DSS} = 75V$
 $I_{D25} = 230A$
 $R_{DS(on)} \leq 4.2m\Omega$

N-Channel Enhancement Mode
Avalanche Rated



TO-263 (7-lead)



Pins: 1 - Gate
 2, 3 - Source
 5,6,7 - Source
 TAB (8) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	75	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	75	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ C$	230	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	700	A
I_A	$T_C = 25^\circ C$	115	A
E_{AS}	$T_C = 25^\circ C$	850	mJ
P_D	$T_C = 25^\circ C$	480	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
T_{sold}	Plastic body for 10 seconds	260	$^\circ C$
Weight	TO-263	3	g

Features

- International standard package
- $175^\circ C$ Operating Temperature
- High current handling capability
- Avalanche rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

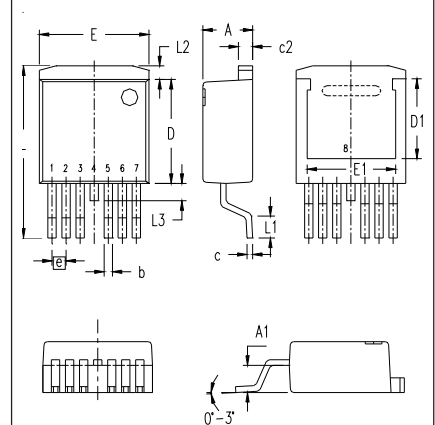
Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 150^\circ C$			150 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2			4.2 $m\Omega$

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1	50	85	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		10.5	nF
C_{oss}			1165	pF
C_{rss}			125	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		23	ns
t_r			18	ns
$t_{d(off)}$			33	ns
t_f			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		178	nC
Q_{gs}			53	nC
Q_{gd}			41	nC
R_{thJC}				0.31 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			230 A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			900 A
V_{SD}	$I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 115\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 37\text{V}$		66	ns
I_{RM}			4.4	A
Q_{RM}			145	nC

TO-263 (7-lead) (IXTA..7) Outline



- Pins: 1 - Gate
 2, 3 - Source
 4 - Drain
 5, 6, 7 - Source
 Tab (8) - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

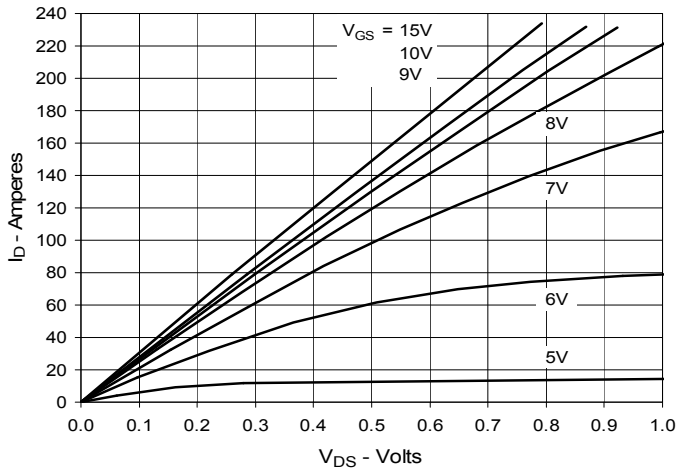
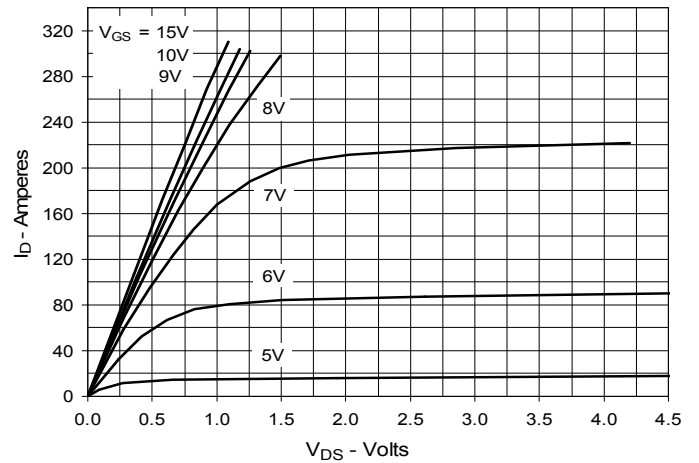
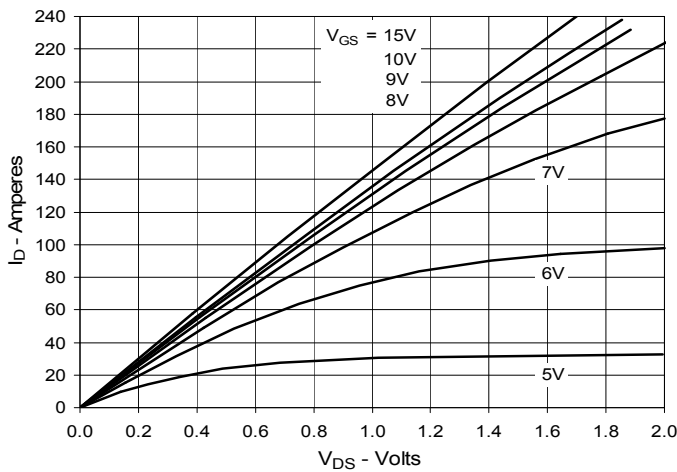
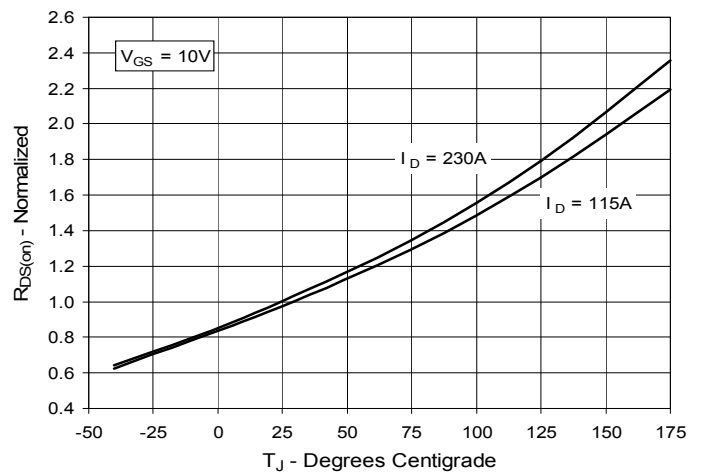
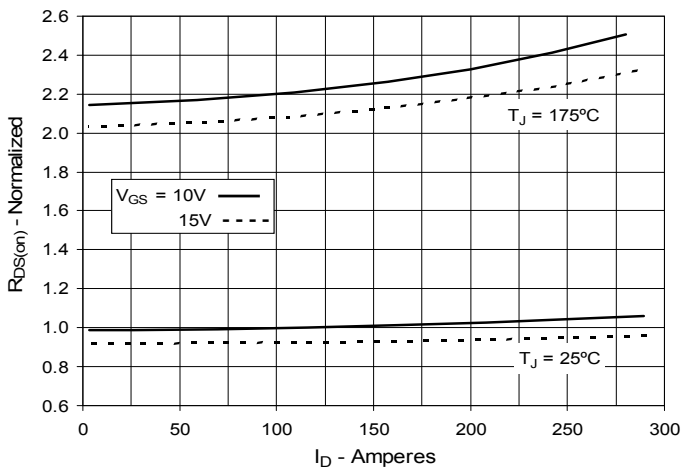
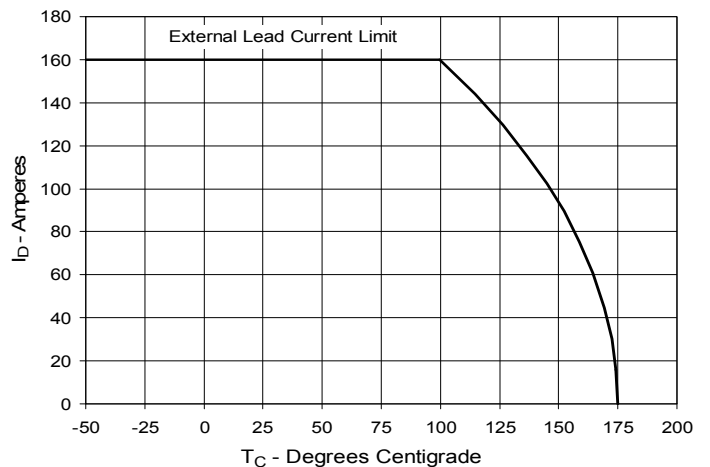
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 150°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 115A$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 115A$ Value
vs. Drain Current**

Fig. 6. Drain Current vs. Case Temperature


Fig. 7. Input Admittance

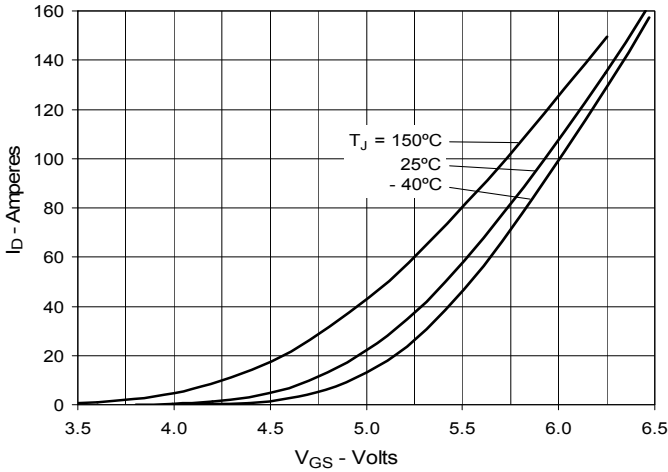


Fig. 8. Transconductance

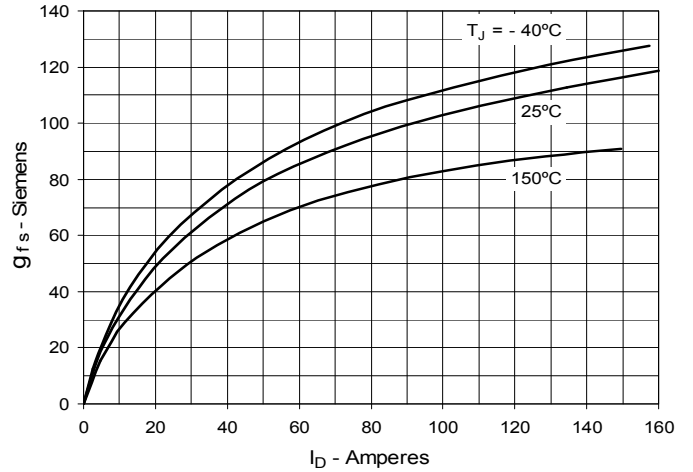


Fig. 9. Forward Voltage Drop of Intrinsic Diode

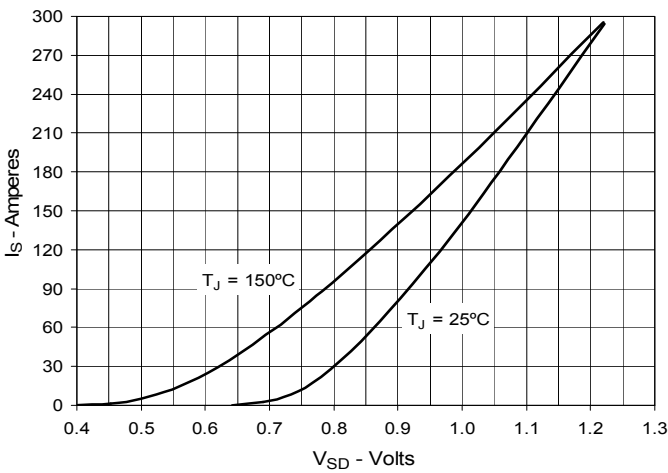


Fig. 10. Gate Charge

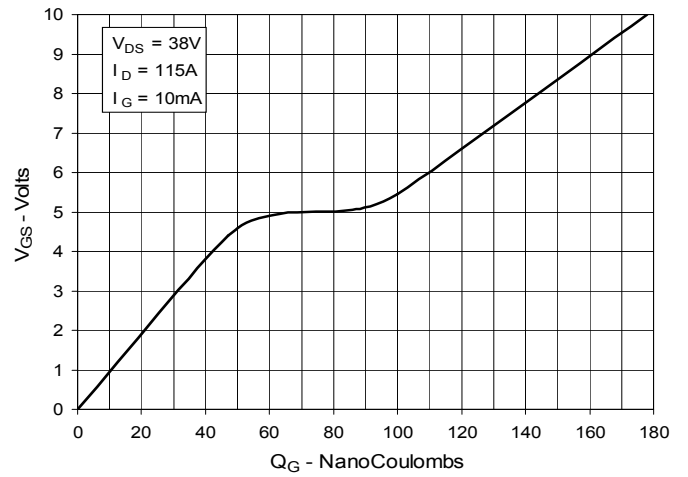


Fig. 11. Capacitance

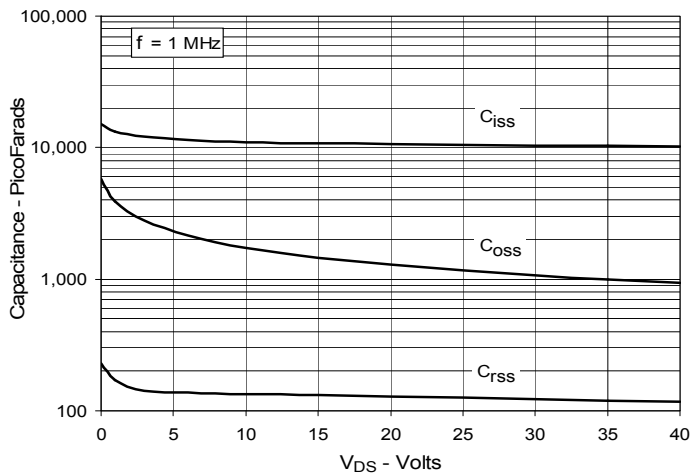
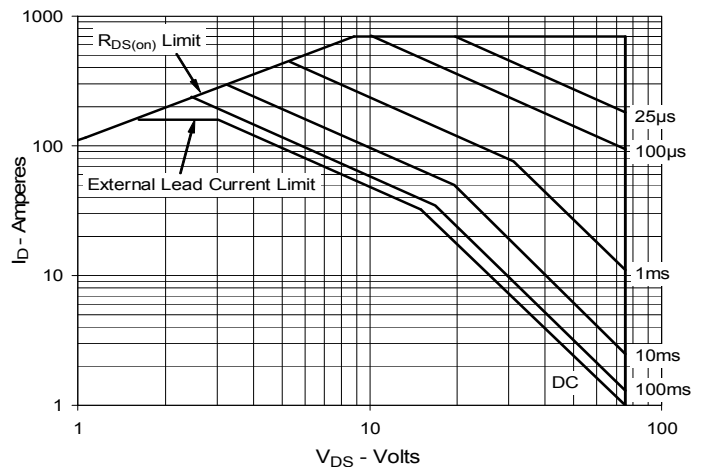


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

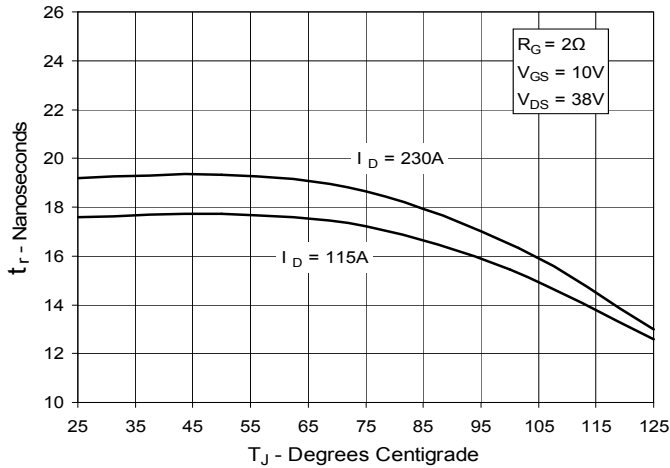


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

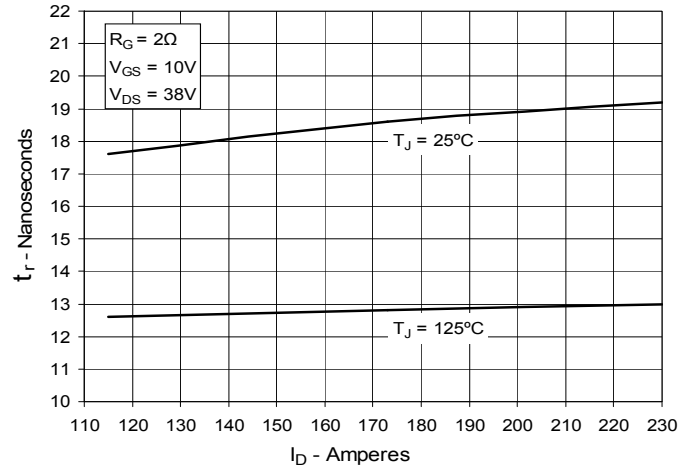


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

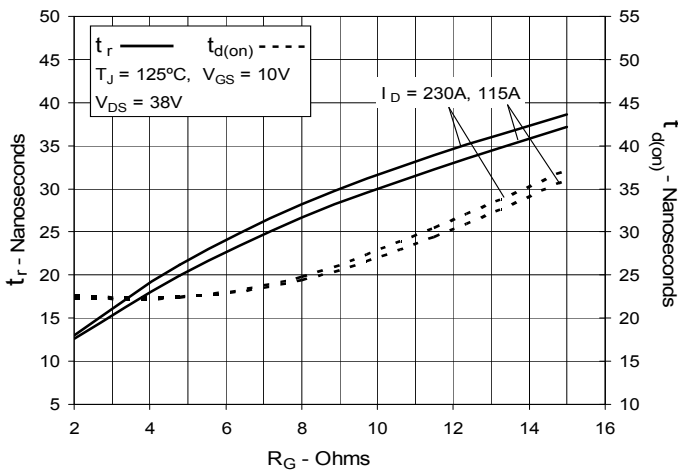


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

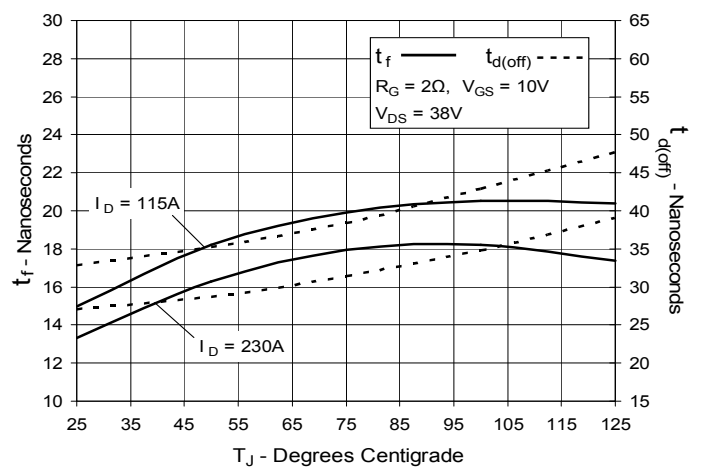


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

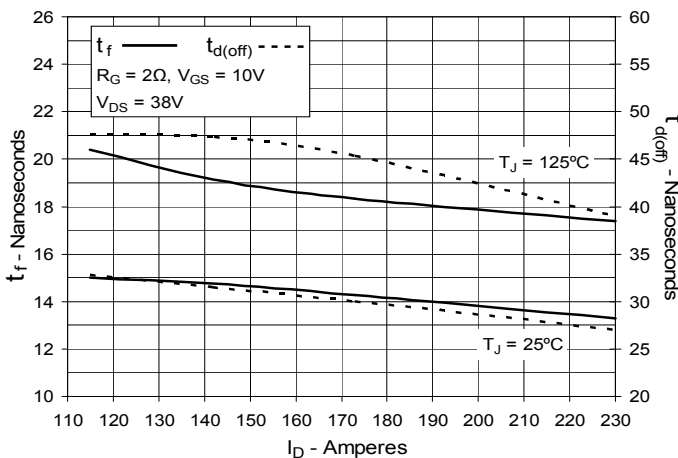


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

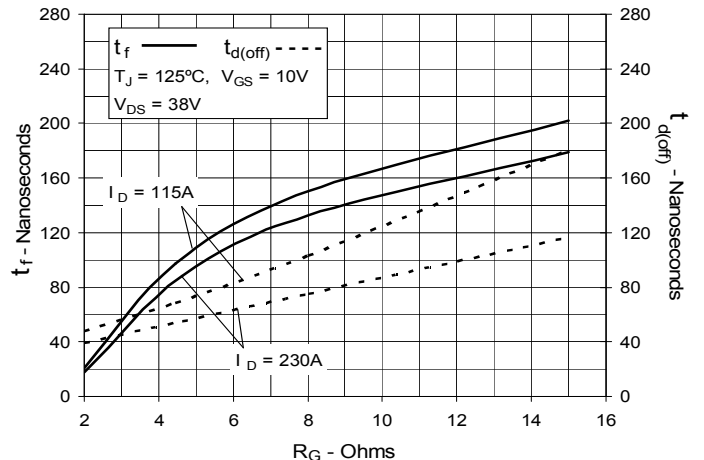


Fig. 19. Maximum Transient Thermal Impedance

